

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
10 February 2005 (10.02.2005)

PCT

(10) International Publication Number
WO 2005/013350 A1

(51) International Patent Classification⁷: **H01L 21/331**,
29/417

(21) International Application Number:
PCT/IB2004/051292

(22) International Filing Date: 26 July 2004 (26.07.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03102405.2 1 August 2003 (01.08.2003) EP

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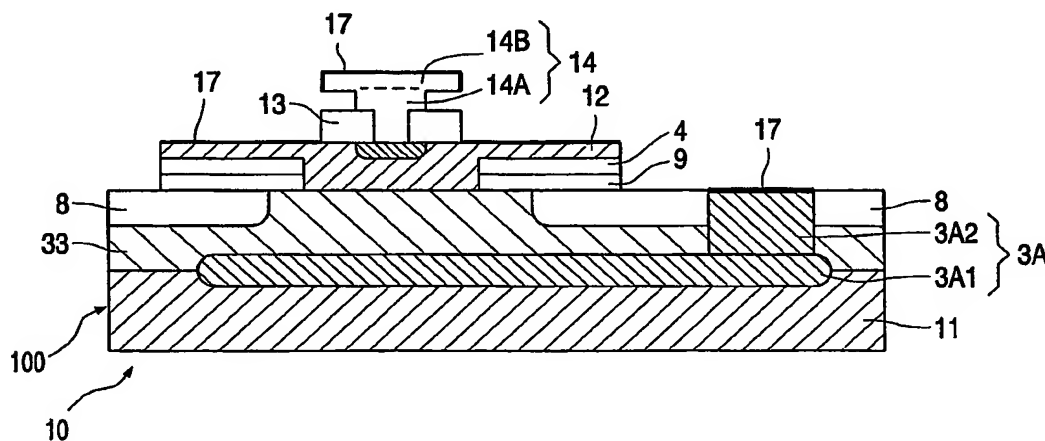
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: **METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE WITH A BIPOLAR TRANSISTOR AND DEVICE WITH A BIPOLAR TRANSISTOR**



(57) Abstract: The invention relates to the manufacturing of a bipolar transistor device (10) in which the emitter is formed using a polycrystalline silicon region (14) which is present in a window in an insulating layer (13) and which extends laterally over said insulating layer (13). The silicon region (14) as well as another silicon region (12) bordering the stack of insulating region (13) and silicon region (14) are silicided by means of a metal layer (16) deposited over the structure. The sideface of the stack is provided with means to avoid bridging of the silicides (17) to be formed. According to the invention the means to prevent bridging of the silicides to be formed comprises that the side face of the stack is structured in such a way that the distance between the upper surface of the silicon region (14) and the upper surface of the other silicon region (12) along the surface of the side face of the stack is made longer than the total thickness of the insulating layer (13) and the semiconductor layer (14). Through the increased path by either a positive or negative slope of the side face of the stack, the bridging of silicides is avoided. Preferred embodiments relate to how the side face of the stack is structured.



ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)

Declaration under Rule 4.17:

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA,

Published:

- with international search report
— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

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